

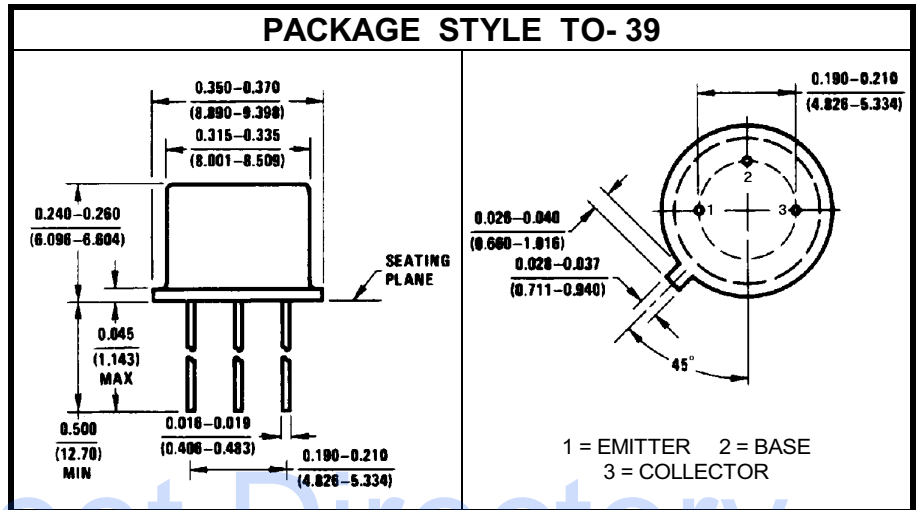
SILICON NPN TRANSISTOR

DESCRIPTION:

The **2N2243A** is Designed for General Purpose Amplifier and Switching Applications.

MAXIMUM RATINGS

I_C	1.0 A (PEAK)
V_{CE}	80 V
P_{DISS}	2.8 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	62.5°C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS	
BV_{CEO}	$I_C = 25\text{ mA}$		80			V	
BV_{CBO}	$I_C = 100\ \mu\text{A}$		120			V	
I_{CBO}	$V_{CB} = 60\text{ V}$				0.01	μA	
	$T_A = 150^\circ\text{C}$				15		
BV_{EBO}	$I_E = 100\ \mu\text{A}$		7.0			V	
I_{EBO}	$V_{EB} = 5.0\text{ V}$				0.05	μA	
h_{FE}	$V_{CE} = 10\text{ V}$	$I_C = 100\ \mu\text{A}$	1530				
		$I_C = 10\text{ mA}$	30				
	$V_{CE} = 1.0\text{ V}$	$I_C = 10\text{ mA}$	$T_A = -55^\circ\text{C}$	20			---
		$I_C = 150\text{ mA}$		30			
		$I_C = 500\text{ mA}$		15		120	
$V_{CE(SAT)}$	$I_C = 150\text{ mA}$	$I_B = 15\text{ mA}$			0.25	V	
$V_{BE(SAT)}$	$I_C = 150\text{ mA}$	$I_B = 15\text{ mA}$			1.3	V	
f_t	$V_{CE} = 10\text{ V}$	$I_C = 50\text{ mA}$	$f = 20\text{ MHz}$	50		MHz	
C_{ob}	$V_{CB} = 10\text{ V}$		$f = 1.0\text{ MHz}$		15	pF	